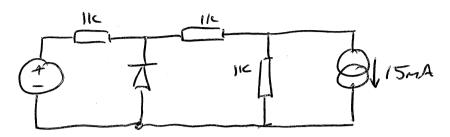
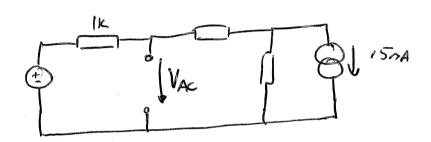
By SUPARPOSITION:



IF DOOR NOT CONDUCTING ...



FOR GU SOURCE (15mAIS O/c)

·. VAC = -6 · 21C

FOR 15 mA Source (6V 23 S/c)

: VAC = 15 x 10 - 1/2 . 1KR = 5V

THIS IS BECAUSE WITH THE GU S/C THE CET BECOMES ,...

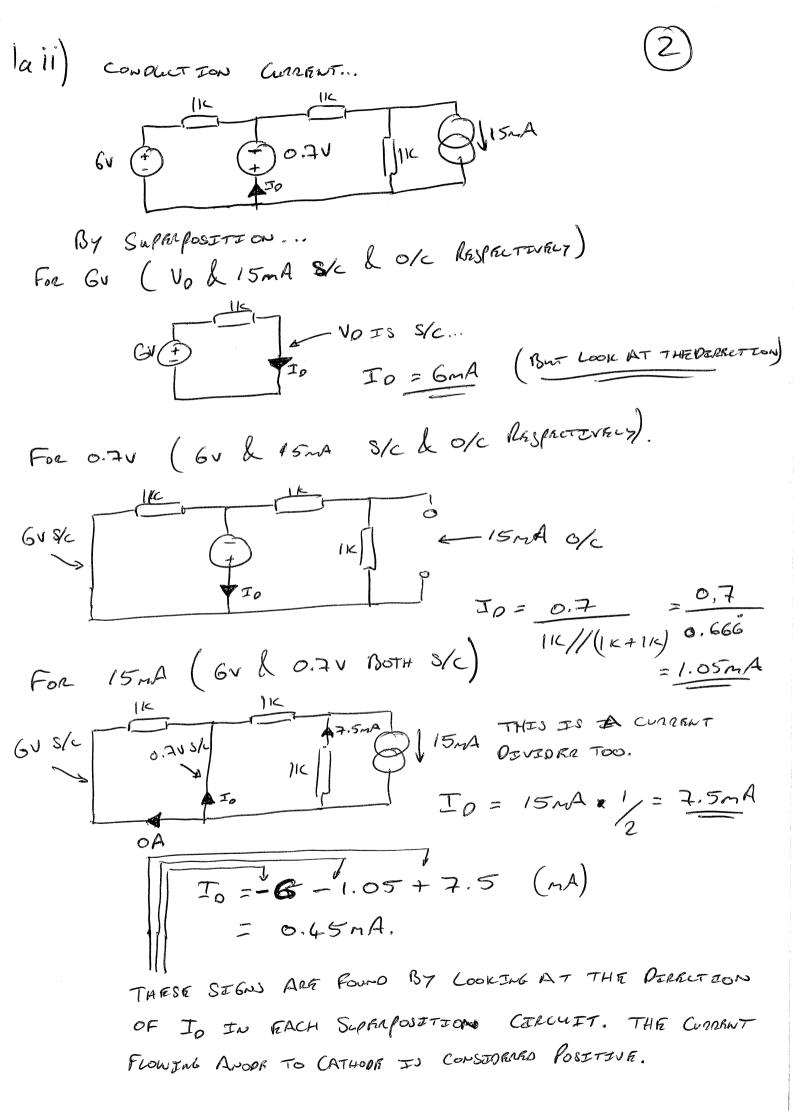
RI JIK 11K BUSALISMA

... WHICH IS A CURRENT DIVIDER CIRCUIT.

From -6. R2+R3

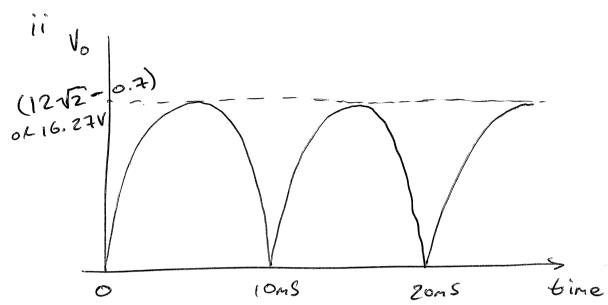
TOTAL NAC = 5V- 4V = IV . IV > 0.7V :

OJOOR CONDLICTS.



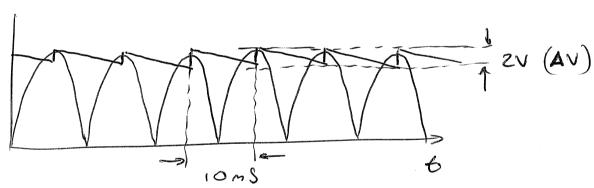
161 Fun WAVE.

(3)



IV LOOKS LIKE

Vo



Δt

ASSUMING LORST CASE (PRAK CURRENT FLOWS AHWAYS)

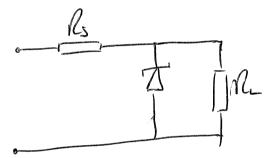
$$I = C dy : C = I dt = \frac{542.3 \cdot 10^{3} \times 10 \times 10^{3}}{2}$$

$$= \frac{2,711.5 \text{ mF}}{2}$$

$$I_{MEN} = \frac{16.27 - 2}{30} = 475.6 \text{ nA}$$

AN OTHER ANSWERS VALTO AS LONG AS ASSUMPTEONS ARE DEASONABLE AND STATED.

di)



ii) MUST USE SMAIRST  $\mathbb{Z}/p$  VOLTAGE & LARGEST O/P

CURRENT.

VO(RECTSFZER)

SOUTH

TR = 500MA + 4MA

= 504 MA

VRS = 14.27 - 9

VRS = 14.27 - 9 Palluti

iii) P=I2R= 2.65 WATTS

:. > 3 W BUT < 10 WATT. WOULD BROK.

iv) Po= Vo x Io

1

9v
(ZENER)

- WHEN CCT IS FULLY ON ID IS A
MINIMUM AT 4NA 801  $P = 9.4 \times 10^{-3} = 36 \text{mW}$ 

- WHEN CUT IS ON STANDBY ID IS

A MAXIMUM (ASSUMTAG THAT "NO LOAD"

IS NOT A VALTO OFTEON)

P= 9, (504-20) MA = 4.356WATT)

IT IS OK TO INCLUDE B-E DESIPATION IF IT'S DONE COLLECTY.

$$V)$$
  $I_B = I_{CV} = \frac{4.69}{100} = 46.9 \text{ A}$ 

VI) POWER IN THE SWETCH SHOULD BE CONSTANT SO

4.69 A

$$fds(on) = \frac{5.159}{4.69^2} = 0.23572$$



$$-J_1 = \frac{V_S - V_D}{7K} = \frac{9-2}{7K} = \frac{1mA}{7K}$$

$$-I_{R} = V_{R}/= 1.3V = 3.02nA$$

$$V_{L} = 1.21c \cdot 302 \text{ mA} = 3.6240$$

$$A = V_s = V_s = V_s = Q = 3.624 = \frac{5.376}{2}$$

$$Tc = 3.02 \text{ mA}$$
  
 $1.006 = \frac{3mA}{1}$ 

$$I_{S} = I_{E} - I_{C} = 3.02 - 3 (mA)$$

$$= 29\mu A$$

$$g_{m} = \frac{e T c}{K T} = \frac{1.6 \times 10^{-19} \cdot 3mA}{1.38 \times 10^{-23} \cdot 300}$$

$$= 0.1159 \text{ A/J}$$

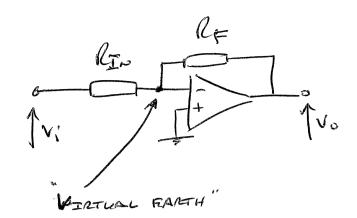
 $V_{V}' = 0.1159 - 1.21c - (1.2941c//7 |c//21c)$  Goo + (1.2941c//7 |c//21c)

= 0.1+59 - 1-2k . 706,387 1,3064

z 75.202 V/V.

(DAPAROS ON ASSUMPTIONS)





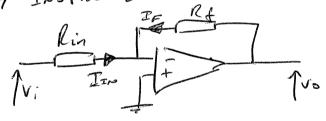


THE VIRTUAL EARTH EXISTS DUR TO THE OPANY OPPRATION.

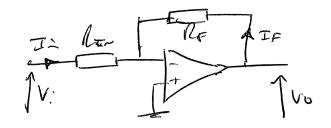
THE OPANY IS DESCRIBED BY ITS EQUATION VO = AU (V+ V).

ASSUMENT AV IS LARGE, THE OPANY WILL, WHEN OPPRENTED WITH NEGATIVE FREDBACK, ATTEMPT TO BRING ITS INPUTS TOGETHERSY ADJUST IND ITS OUTPUT VOLTAGE. SINCE THE NON-INVENTING INPUT IS GROWNORD THE OPANY WILL ATTEMPT. TO MAKE THE INVENTING INVENTING INPUT IS GROWNORD THE OPANY WILL ATTEMPT. TO MAKE THE INVENTING INVENTING INPUT IS GROWNORD THE OPANY WILL ATTEMPT. TO MAKE THE

iv) By INSPRCT ION THE INPUT RESISTANCE IS RIN.



$$\frac{V: -V^{-}}{Rin} = \frac{V^{-}-V_{o}}{R_{F}}$$



$$\frac{V_0 - V^-}{R_F} + \frac{V_1^- - V^-}{R_{in}} = 0$$

USR V- IN 
$$V_0 = A_V(V^+ - V^-)$$
 AND  $\frac{V^+ = 0}{2}$ 

As 
$$V^+ = 0$$

... P. SOME TRAMBFOSTTEON ...

## 66) SEVERAL ROSSER METHODS ...

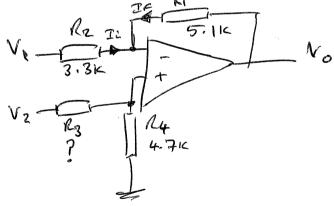
FIRST

$$V_0|_{V_1} = V_1 \cdot \frac{R_2/R_3}{R_1 + R_2/R_3} \cdot \frac{R_5 + R_4}{R_4}$$

THIS IS A KIND OF SUMMING ANGLIFTER. MORE SPECIFICATION IF RISH SPECIFICATION THE AVERAGE OF THE THREE TRAITS MULTIPLIERD BY A GAIN OF RS+R4

$$\frac{V_1 - V^+}{R_1} + \frac{V_2 - V^+}{R_2} + \frac{V_3 + V^+}{R_3} = 0$$

GCi) ALSO SKUGRAL MATHODS ... FIRST.



$$\frac{V_1 - V^{-}}{R_2} + \frac{V_0 - V^{-}}{R_1} = 0 \quad \bigcirc$$

$$V^{+} = V_{2} R_{4}$$
 (3)

$$\left( \left( \textcircled{3} \rightarrow \textcircled{2} \right) \rightarrow \textcircled{1} \right)$$

$$\frac{V_1 - V_2 R_4}{R_3 + R_4} + \frac{V_0 - V_2 R_4}{R_3 + R_4} = 0$$

$$V_{o} = -\left(V_{1} - \frac{V_{2}R_{4}}{\Omega_{3} + R_{4}}\right)R_{1} + \frac{V_{2}R_{4}}{R_{3} + R_{4}}$$

SOLVE (4) FOR R3 TO GET. ..

$$l_{3} = -l_{4} \left(-R_{1} - R_{2}\right) V_{2}$$

$$= -4.7 \left(-5.1 - 3.3\right) \cdot -8$$

$$= 5.621 \text{K}$$

$$= 5.1 \cdot (-6) + 3.3 \cdot 0$$

SECOND METHOD

$$V_{0}|_{V_{1}} = V_{1} - R_{1}$$

$$V_{0}|_{V_{2}} = V_{2} \cdot R_{4} - R_{1} + R_{2}$$

$$R_{2}$$

$$R_{3} + R_{4} - R_{2}$$

$$V_0 = V_1 - h_1 + V_2 \frac{h_4}{R_3 + h_4} \cdot \frac{R_1 + R_2}{R_2} \left(V^+ = V...\right)$$

Sus Vo=0 ,...

$$-1. V_1 - R_1 = - \frac{V_2 R_4}{R_3 + R_4} \cdot \frac{R_1 + R_2}{R_2}$$

SOLVE FOR Rg --

$$R_3 = \frac{V_2(R_4R_1 + R_4R_2)R_2 - V_1R_1R_4R_2}{V_1R_1R_2}$$

SUBSTITUTE VALUES.

$$R_{3} = -8(4.7.5.1+4.7.3.3)3.3-(-6)5.1.4.7.3.3$$

$$(-6)5.1.3.3$$

THIRD MATHOD

$$\frac{V_1-V}{2}+\frac{V_0-V}{R_1}=0$$

$$\frac{V_2 - V^+}{R_3} = \frac{V^+}{R_4} = \frac{2}{\sqrt{2}} \Rightarrow \left(V_2 + V^+\right) R_4 = V^+ R_3$$

$$\left(V_2 - \frac{V_1 R_1 + V_0 R_2}{R_1 + R_2}\right) R_4 = \frac{V_1 R_1 + V_0 R_2}{R_1 + R_2}. R_3$$

 $R_{4}V_{2}(R_{1}+R_{2}) - V_{1}R_{1}R_{4} + V_{0}R_{2}R_{4} = V_{1}R_{1}R_{3} + V_{0}R_{2}R_{3}$   $V_{0}(R_{2}R_{4} - R_{2}R_{3}) = V_{1}R_{1}R_{3} - V_{2}(R_{1}+R_{2})R_{4} + V_{1}R_{1}R_{4}$   $V_{0} = V_{1}R_{1}R_{3} - R_{4}V_{2}(R_{1}+R_{2}) + V_{1}R_{1}R_{4}$   $R_{2}R_{4} - R_{2}R_{3}$   $V_{0} = V_{1}(R_{1}R_{3} + R_{1}R_{4}) - V_{2}(R_{1}+R_{2})R_{4}$   $R_{2}(R_{4} - R_{3})$  = -G(5.1(5.621 + 4.7)) - (-8)(5.1+3.3)4.7 3.3(4.7 - 5.621)  $= \sim 0.0174V$   $S_{0} = 5.621 \text{ KeV} = 5.621$   $= \sim 0.0174V$   $S_{0} = 5.621 \text{ KeV} = 5.621$ 

## EEE 118 2014 Solutions

(i)

Q2 (a)
$$R = \frac{dV}{dR} = \frac{1}{slope} 2$$
reverse bias of forward bias
$$note \ aurent = 0 \ at \ V = 0$$

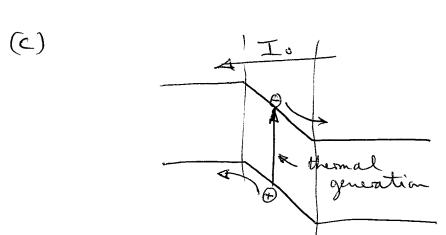
As I in reases slope increases and R decreases.

(b) hole current & 
$$\sigma_p = pe_Mh$$
  
electron current &  $\sigma_n = ne_Me$ 

Injection efficiency 
$$S = \frac{I_P}{I_P + I_P}$$

$$= \frac{\sigma_{p}}{\sigma_{p} + \sigma_{n}} = \frac{1}{1 + \frac{\sigma_{n}}{\sigma_{p}}} = \frac{1}{1 + \frac{7 \times 10^{23} \times 0.07}{7 \times 10^{25} \times 0.045}}$$

From page 1 
$$\alpha = 815 = 0.985$$
  
when  $\beta = \frac{\alpha}{1-\alpha} = \frac{0.985}{1-0.985}$ 



In reverse hias the depletion region is extended and the barrier to diffusion is increased. Latter is cut off but themally generated carriers 3 produce small reverse current as shown.

- (i) Increased bond-gap reduces the possibility of electron-hole thermal generation hence I To would decrease.
- (ii) Lover temperature provides less energy hence reduced Io.

(d) 
$$I = I_0 \left( \exp \frac{eV}{kT} \right)$$
ignore

i exper = I

 $V = kI ln = \frac{1.38 \times 10^{-23} \times 300 ln \frac{10^{-2}}{10^{-6}}$  = 0.24 V

A stual deminal voltage greater than this due to voltage drop a cross semiconductor either side of junction.

2

 $\frac{Q4}{(a)}$ 

(i) JFET

Substati

de pletion region

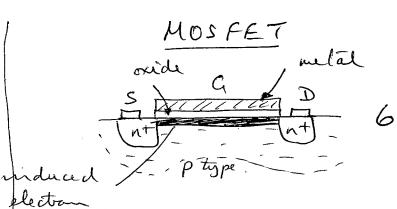
pare depletes channel and restricts electron flow from S to D (Is). Initial amount at low do

hital ament at low drawn bras due to resistance of the channel

To Vg more negative

As VD becomes more regative channel resistance in creases until it is pinched off - ID then saturates

Device is on " hen no you bias is applied "normally on"). "OH" ohen V > V pinch-A.



Position gate bias causes depletion of p-type region.
No channel or current initially As gate brias increases, electron channel is induced under 2 the gate and get conduction between S + D. at Vq = Vth

in Grasinos

A Vg

4

As VD increases, voltage between G+D at drain end reduces intil Vg-Vo ZVon 2 and drained is prinched off - ID saturates.

(ii) Device is off with no gote bias (notwally off"). "On" when  $V_g > V_{th}$ .

channel is fully depleted velocity v= µ E = 0.07 x 5 x 10 6 ms -1 = 3.5×105 ms-1 Time to travel under gate =  $\frac{Lg}{v} = \frac{1\times10^{-6}}{3.5\times10^{5}}$ = 2.86 ps (2.86×10-12s) (ii) The transit time under the gate determines how quickly charge can be removed from the channel or gate, Hence the device counset charge state (egion" or off") faster than this and switching speed is

limited by this delay.

The born atom has Souter electrons and when it boards to a Si lattice there is IV electron too few for a complete board. Hence 6 the missing electron represents a hole with a net (4) we there. The born atom appears to have a net negative charge when the hole moves away.

(b) Since the hole concentration is dependent on the boron concentration only at room 2 temperature and above, it will not change significantly. In undoped material there is much less electrons and holes but these will increase in concentration 2 as the temperature is in creased giving that to a larger fractional in crease.

(c) From page 1 
$$n_p p_p = n_i^2$$
 3
$$\frac{1 \times 10^{32}}{p_p} = \frac{1 \times 10^{32}}{1 \times 10^{24}} = \frac{1 \times 10^8 \text{ m}^{-3}}{1 \times 10^{24}}$$

(d) From page 1  $\sigma = n_p e p e + p_p e p h$ .

ignore electron contribution since this is

very small

$$= \frac{7.2 \times 10^{24} \times 1.6 \times 10^{-19} \times 0.045}{10^{-19} \times 10^{24} \times 10^{-19}}$$

(e) for electrons 
$$\sigma_e = n_p e \mu_e$$

$$= 1 \times 10^8 \times 1.6 \times 10^{-19} \times 0.07$$

$$= 1.12 \times 10^{-12} \text{ Sm}^{-1}$$
ie. it is indeed nightigible

(4)

$$=\frac{1 \text{ mm}}{7.2 \times 10^{3} \times (1 \text{ mm})^{2}}$$

$$=\frac{1 \text{ mm}}{7.2 \times 10^{3} \times (1 \text{ mm})^{2}} = \frac{10^{3}}{7.2 \times 10^{3} \times 1 \times 10^{-6}}$$

(9) 
$$R_{2mn} = \frac{2 \times 10^{-5}}{7.2 \times 10^{3} \times 4 \times 10^{-6}}$$